

NCE Automotive N-Channel Super Trench Power MOSFET

Description

The NCEAP40T13AGU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS}(\text{ON})}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

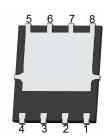
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =40V, I_D =165A (Silicon Limited) $R_{DS(ON)}$ =2.0m Ω (typical) @ V_{GS} =10V
- Excellent gate charge x RDS(on) product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- AEC-Q101 qualified

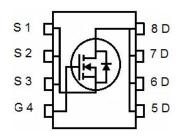
DFN 5X6





Top View

Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP40T13AGU	NCEAP40T13AGU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous (Silicon Limited)(Note 1)	I _D	165	А
Drain Current-Continuous	I _D (100°C)	129	А
Drain Current-Continuous (Package Limited)	I _D	130	А
Pulsed Drain Current	I _{DM}	520	А
Maximum Power Dissipation	P _D	156	W
Derating factor		1.04	W/°C
Single pulse avalanche energy (Note 2)	E _{AS}	480	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{eJC}	0.96	°C/W
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NCEAP40T13AGU

Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			<u>.</u>	•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics			<u> </u>			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2	2.8	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	2.0	2.6	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A		60	-	S
Dynamic Characteristics						
Input Capacitance	Clss	V _{DS} =20V,V _{GS} =0V,	-	2165	2814	PF
Output Capacitance	Coss		-	1061	1379	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	66	99	PF
Switching Characteristics (Note 1)						
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DD} =20 V , I_D =20 A	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Qg	\/ 00\/ L 00A	-	34	44.2	nC
Gate-Source Charge	Q _{gs}	V _{DS} =20V,I _D =20A,	-	10.5	14.7	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	7	10.5	nC
Drain-Source Diode Characteristics			<u>.</u>	•		
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current	Is		-	-	130	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	23	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	62	-	nC

Notes:

- 1. Defined by design.Not Subject to production test
- 2. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=20V,V_G=10V,L=0.5mH,Rg=25 Ω
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics

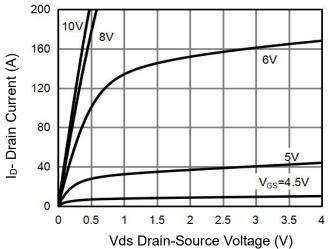


Figure 1 Output Characteristics

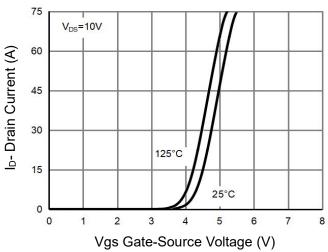
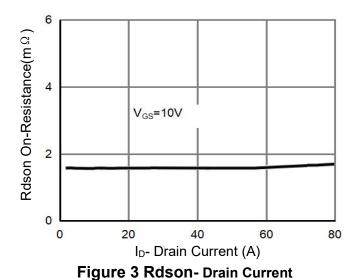


Figure 2 Transfer Characteristics



2 0 1.8 0 1.8 0 25 50 75 100 125 150 175 TJ-Junction Temperature(°C)

Figure 4 Rdson-JunctionTemperature

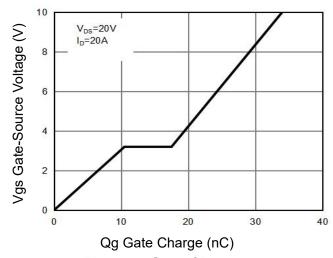


Figure 5 Gate Charge

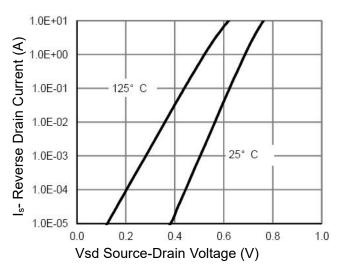


Figure 6 Source- Drain Diode Forward



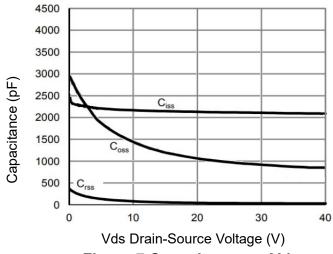


Figure 7 Capacitance vs Vds

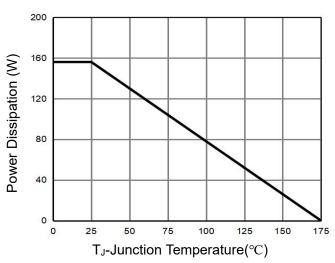


Figure 9 Power De-rating

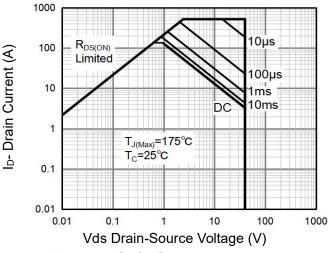


Figure 8 Safe Operation Area (Note4)

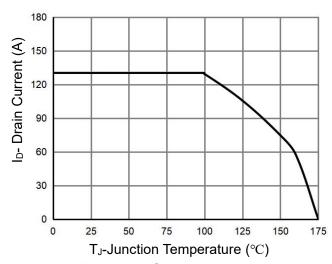


Figure 10 Current De-rating

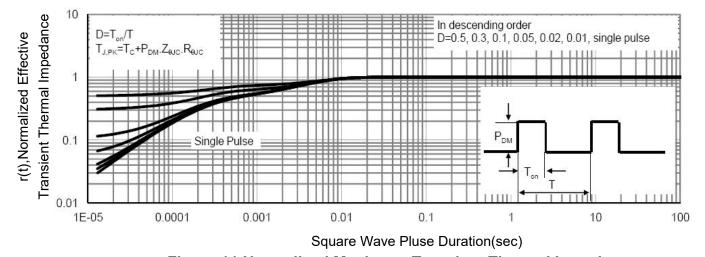
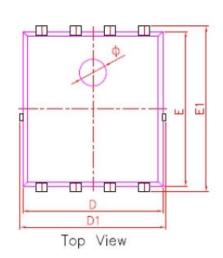
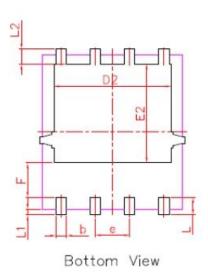


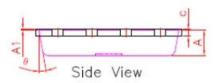
Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information







DIM.	MIN.	NOM.	MAX.	
Α	0.90	0.95	1.00	
A1	0.00	0.02	0.05	
b	0.35	0.40	0.50	
С	0.20	0.25	0.30	
D	5.10	5.20	5.30	
D1	5.10	5.40	5.50	
D2	4.25	4.35	4.45	
е	1.27 BSC			
Е	5.70	5.75	5.80	
E1	6.00	6.15	6.30	
E2	3.57	3.67	3.77	
F	1.18	1.28	1.38	
L	0.55	0.65	0.75	
L1	0.15	0.20	0.25	
L2	0.45	0.55	0.65	
Ø	0.90	1.00	1.10	
Θ	8.	10*	12°	



http://www.ncepower.com

NCEAP40T13AGU

Revision	Date	Subjects	
V1.0	2022.11.12	First version	
V2.0	2023.02.23	Product data sheet	
V3.0	2023.11.16	Ciss Coss Crss Qg Qgs Qgd Max value	

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